

PCN Number:	20180606000	PCN Date:	June 08, 2018
Title:	Datasheet for THS6212		
Customer Contact:	PCN Manager	Dept:	Quality Services
Change Type:			
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design
<input type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Data Sheet
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Site
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Material
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Process
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Fab Site
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Fab Materials
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Fab Process

Notification Details

Description of Change:

Texas Instruments Incorporated is announcing an information only notification. The product datasheet(s) is being updated as summarized below. The following change history provides further details.



THS6212

SBOS758B –MAY 2016–REVISED MAY 2018

Changes from Revision A (March 2017) to Revision B

Page

• Changed full-bias mode value from 21 mA to 23 mA in <i>Features</i> list	1
• Changed mid-bias mode value from 16.2 mA to 17.7 mA in <i>Features</i> list	1
• Changed low-bias mode value from 11.2 mA to 12.2 mA in <i>Features</i> list	1
• Added "With Exposed Thermal Pad" to pinout drawing description to <i>Pin Configuration and Functions</i> section	4
• Deleted I_{S+} quiescent current " $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$ " test conditions and values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted minimum and maximum full bias I_{S+} quiescent current values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Changed typical full bias I_{S+} quiescent current value from 21 mA to 23 mA in <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted minimum and maximum mid bias I_{S+} quiescent current values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Changed typical mid bias I_{S+} quiescent current value from 16.2 mA to 17.7 mA in <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted minimum and maximum low bias I_{S+} quiescent current values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Changed typical low bias I_{S+} quiescent current value from 11.2 mA to 12.2 mA in <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted I_{S-} quiescent current " $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$ " test conditions and values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted minimum and maximum full bias I_{S-} quiescent current values	7
• Changed typical full bias I_{S-} quiescent current value from 20 mA to 22 mA	7
• Deleted minimum and maximum mid bias I_{S-} quiescent current values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Changed typical mid bias I_{S-} quiescent current value from 15.2 mA to 16.7 mA in <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted minimum and maximum low bias I_{S-} quiescent current values from <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Changed typical low bias I_{S-} quiescent current value from 10.2 mA to 11.2 mA in <i>Electrical Characteristics: $V_S = \pm 12\text{ V}$</i> table	7
• Deleted I_{S+} quiescent current " $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$ " test conditions and values from <i>Electrical Characteristics: $V_S =$</i>	7

6 V table	10
• Deleted minimum and maximum full bias I_{S+} quiescent current values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical full bias I_{S+} quiescent current value from 17 mA to 18.6 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted minimum mid bias I_{S+} quiescent current value from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical mid bias I_{S+} quiescent current value from 13.2 mA to 14.4 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted minimum and maximum low bias I_{S+} quiescent current values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical low bias I_{S+} quiescent current value from 9.4 mA to 10.2 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted I_{S-} quiescent current " $T_A = -40^{\circ}C$ to $+85^{\circ}C$ " test conditions and values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted minimum and maximum full bias I_{S-} quiescent current values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical full bias I_{S-} quiescent current value from 16 mA to 17.6 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted minimum and maximum mid bias I_{S-} quiescent current values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical full bias I_{S-} quiescent current value from 12.2 mA to 13.4 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Deleted minimum and maximum low bias I_{S-} quiescent current values from <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed typical low bias I_{S-} quiescent current value from 8.4 mA to 9.2 mA in <i>Electrical Characteristics: $V_S = 6 V$</i> table	10
• Changed Quiescent Current for Full Bias Setting vs R_{ADJ} graph	13
• Changed Quiescent Current for Mid Bias Setting vs R_{ADJ} graph	15
• Changed Supply Current for Low Bias Setting vs R_{ADJ} graph	17
• Changed Quiescent Current for Full Bias Setting vs R_{ADJ} graph	20
• Changed Quiescent Current for Mid Bias Setting vs R_{ADJ} graph	22
• Changed Quiescent Current for Low Bias Setting vs R_{ADJ} graph	24
• Changed quiescent current value from 21 mA to 23 mA in <i>Wideband Current-Feedback Operation</i> section	30
• Changed quiescent current value from 21 mA to 23 mA in paragraph above Equation 19	36
• Changed 21 mA to 23 mA and 955 mW to 1003 mW in Equation 19	36
• Changed <i>Board Layout Guidelines</i> section title to <i>Layout Guidelines</i> to align with standards	37

The datasheet number will be changing.

Device Family	Change From:	Change To:
THS6212	SBOS758A	SBOS758B

These changes may be reviewed at the datasheet links provided.

<http://www.ti.com/product/THS6212>

Reason for Change:

To accurately reflect device characteristics.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

No anticipated impact. This is a specification change announcement only. There are no changes to the actual device.

Changes to product identification resulting from this PCN:

None.

Product Affected:

THS6212IRHFR	THS6212IRHFT		
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For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
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